# 2SD2209

## Silicon NPN triple diffusion planar type Darlington

For power amplification and switching

### Features

• I type package enabling direct soldering of the radiating fin to the printed circuit board, etc. of small electronic equipment.

### Absolute Maximum Ratings (T<sub>C</sub>=25°C)

Parameter	Symbol	Ratings	Unit
Collector to base voltage	V <sub>CBO</sub>	100±15	V
Collector to emitter voltage	e V <sub>CEO</sub>	100±15	V
Emitter to base voltage	V <sub>EBO</sub>	5	V
Peak collector current	$I_{CP}$	8	A
Collector current	$I_{\rm C}$	4	A
Collector power T <sub>C</sub> =25°C		15	W
dissipation Ta=25°C	$P_{C}$	1.3	W
Junction temperature	T <sub>j</sub>	150	°C
Storage temperature	$T_{\rm stg}$	-55 to +150	°C

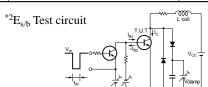
# 7.0±0.3 3.0±0.2 2.3±0.2 4.6±0.4 1 2 3 1:Base 2:Collector 3:Emitter I Type Package Unit: mm 3.5±0.2 Unit: mm 3.5±0.2 1:Base 2:Collector 3:Emitter I Type Package Unit: mm 3.5±0.2 1:Base 2:Collector 3:Emitter I Type Package 1:Base

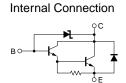
### Electrical Characteristics (T<sub>C</sub>=25°C)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = 85V, I_{E} = 0$	70	$\nabla_{\mathbb{Q}_{p_{n}}}$	100	μА
Emitter cutoff current	I <sub>EBO</sub>	$V_{EB} = 5V, I_C = 0$	\ \ \ \C		2	mA
Collector to emitter voltage	$V_{CEO}$	$I_C = 5 \text{mA}, I_B = 0$	85		115	V
Forward current transfer ratio	h <sub>FE1</sub>	$V_{CE} = 3V, I_{C} = 0.5A$	1000			
	h <sub>FE2</sub> *1	$V_{CE} = 3V, I_{C} = 3A$	1000		10000	
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 3A, I_B = 12mA$			2	V
		$I_{\rm C} = 5 \text{A}, I_{\rm B} = 20 \text{mA}$			4	
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_C = 3A, I_B = 12mA$			2.5	V
Transition frequency	$f_{T}$	$V_{CE} = 10V, I_C = 0.5A, f = 1MHz$		20		MHz
Turn-on time	t <sub>on</sub>	1-3A I 12m A I 12m A			0.3	μs
Storage time	t <sub>stg</sub>	$I_C = 3A$ , $I_{B1} = 12mA$ , $I_{B2} = -12mA$ ,			3.0	μs
Fall time	t <sub>f</sub>	$V_{CC} = 50V$			1.0	μs
Energy handling capability	E <sub>s/b</sub> *2	$I_C = 1A, L = 100 \text{mH}, R_{BE} = 100 \Omega$		50		mJ

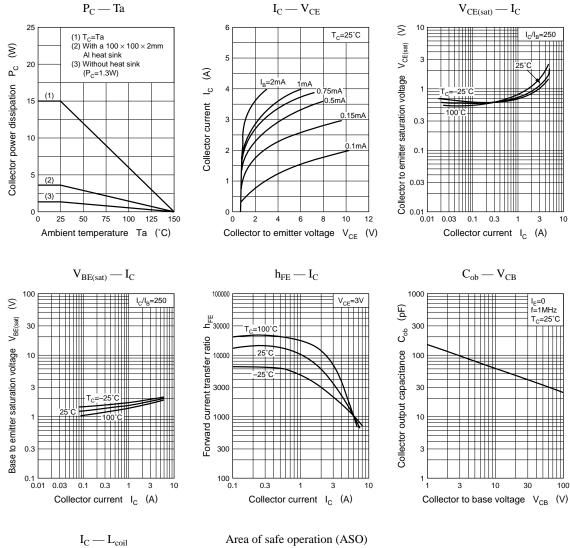
$^{*1}h_{FE2}$ Rank	classification
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Rank	Q	P
h <sub>FE2</sub>	1000 to 5000	2000 to 10000

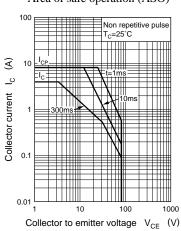




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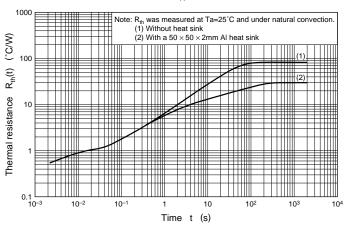


100 30 (V) 10 10 0.3 0.1 1 3 10 30 100 Load inductance L<sub>coil</sub> (mH)



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